

## 4415GH-VB Datasheet

### P-Channel 30-V (D-S) MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>d</sup>	$Q_g$ (Typ.)
- 30	0.033 at $V_{GS} = - 10$ V	- 38	19 nC
	0.046 at $V_{GS} = - 4.5$ V	- 25	

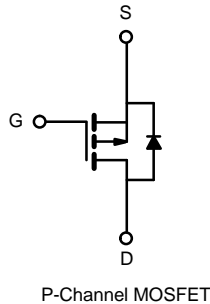
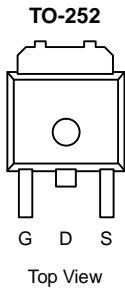
#### FEATURES

- Halogen-free
- Trench Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested


**RoHS**  
 COMPLIANT

#### APPLICATIONS

- Load Switch
- Notebook Adaptor Switch



#### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	- 30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	$I_D$	- 38	A
	$T_C = 70$ °C		- 25	
	$T_A = 25$ °C		- 14.9 <sup>a, b</sup>	
	$T_A = 70$ °C		- 13.6 <sup>a, b</sup>	
Pulsed Drain Current		$I_{DM}$	- 112	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	$I_S$	- 4.1	
	$T_A = 25$ °C		- 2.2 <sup>a, b</sup>	
Avalanche Current	L = 0.1 mH	$I_{AS}$	- 20	mJ
Single-Pulse Avalanche Energy		$E_{AS}$	20	
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	25	W
	$T_C = 70$ °C		20	
	$T_A = 25$ °C		2.7 <sup>a, b</sup>	
	$T_A = 70$ °C		1.7 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 150	°C

#### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, c</sup>	$t \leq 10$ s	$R_{thJA}$	38	46	°C/W
Maximum Junction-to-Foot	Steady State	$R_{thJF}$	20	25	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

 b.  $t = 10$  s.

c. Maximum under Steady State conditions is 85 °C/W.

 d. Based on  $T_C = 25$  °C.

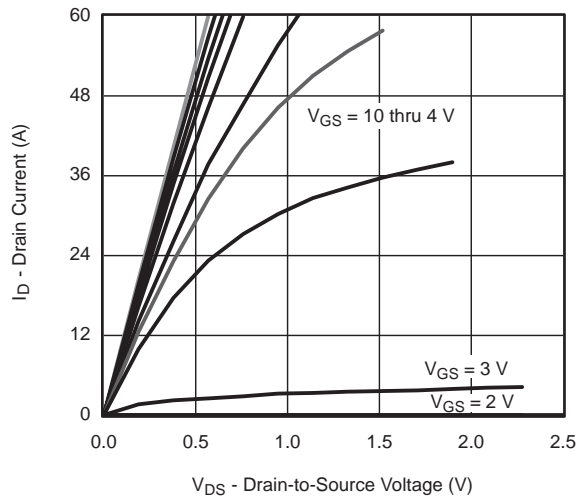
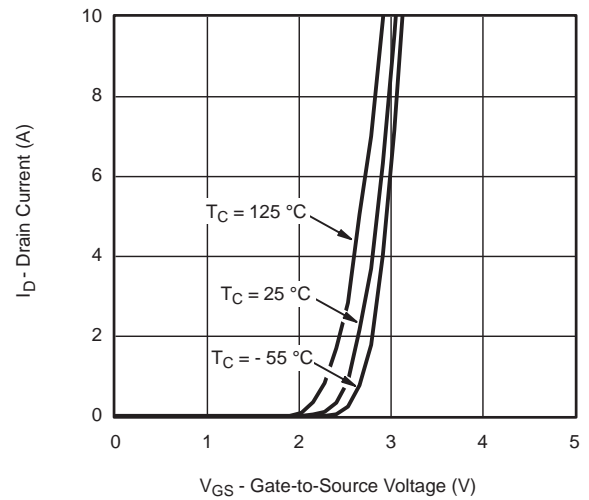
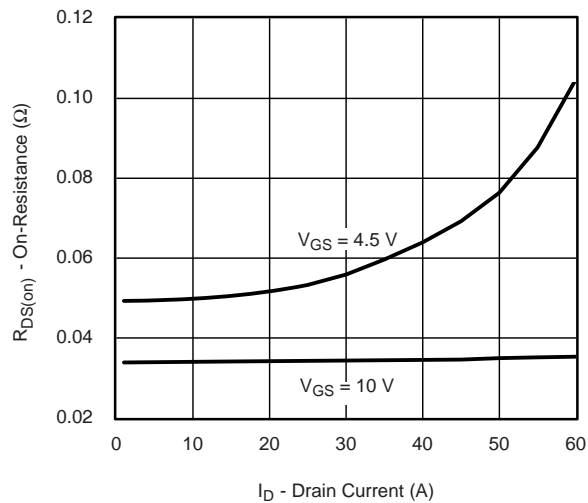
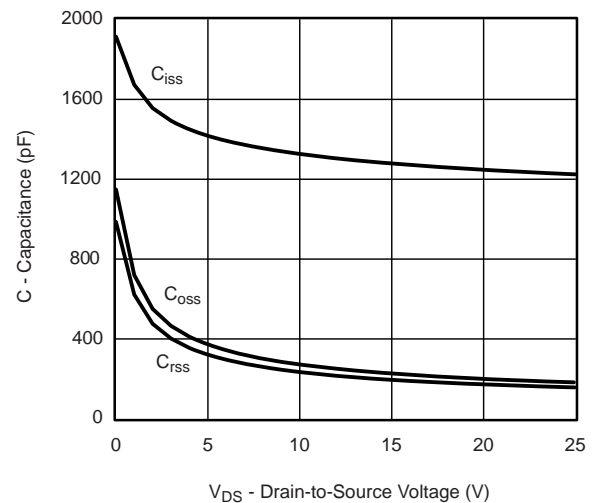
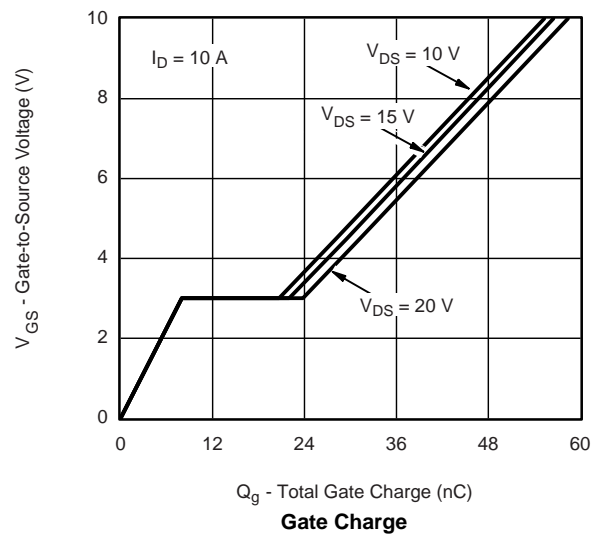
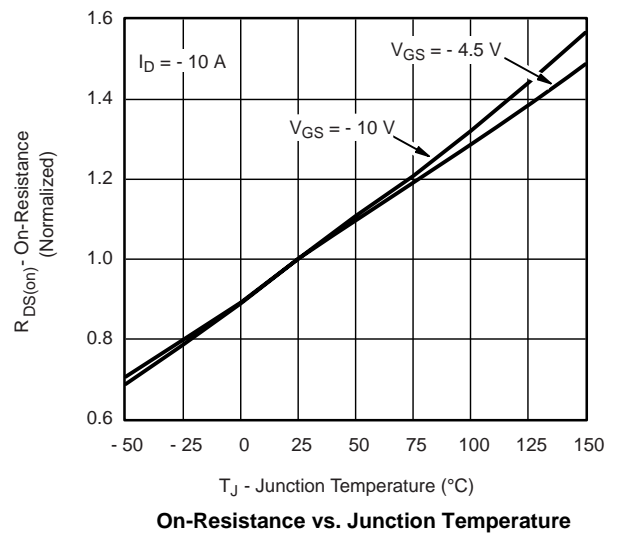
SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 30			V	
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 34		mV/ °C	
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			5.3			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.0		- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 25 V			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	μA	
		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 5		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ - 10 V, V <sub>GS</sub> = - 10 V	- 30			A	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		0.033		Ω	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 8 A		0.046			
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 10 A		28		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1350		pF	
Output Capacitance	C <sub>oss</sub>			255			
Reverse Transfer Capacitance	C <sub>rss</sub>			190			
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		27	43	nC	
		V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 10 A		19	25		
					6		
					12		
Gate-Source Charge	Q <sub>gs</sub>						
Gate-Drain Charge	Q <sub>gd</sub>						
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.2	4.4	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≡ - 10 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 1 Ω		13	25	ns	
Rise Time	t <sub>r</sub>			12	24		
Turn-Off DelayTime	t <sub>d(off)</sub>			40	70		
Fall Time	t <sub>f</sub>			9	18		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≡ - 10 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		48	80		
Rise Time	t <sub>r</sub>			92	160		
Turn-Off DelayTime	t <sub>d(off)</sub>			34	60		
Fall Time	t <sub>f</sub>			19	35		
Drain-Source Body Diode Characteristics							
Continous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 4.1	A	
Pulse Diode Forward Current	I <sub>SM</sub>				- 40		
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 3 A, V <sub>GS</sub> = 0 V		- 0.75	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 10 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C		27	45	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			16	27	nC	
Reverse Recovery Fall Time	t <sub>a</sub>			12		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			15			

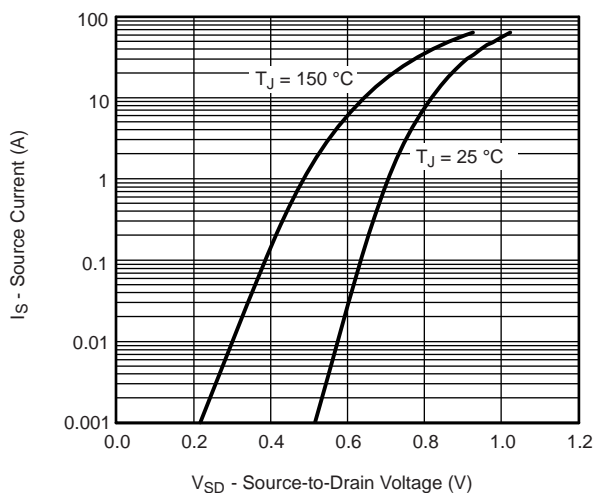
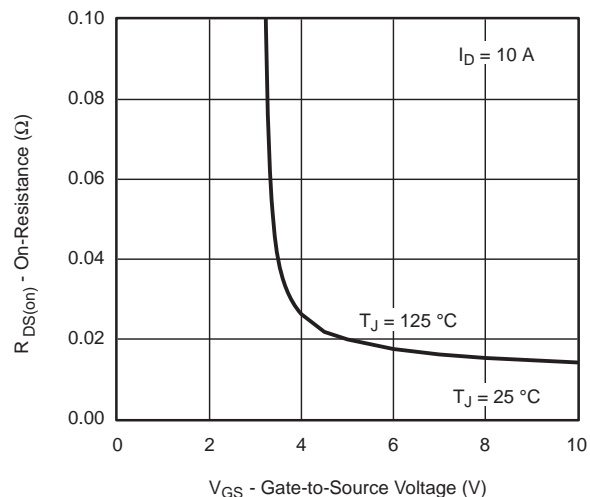
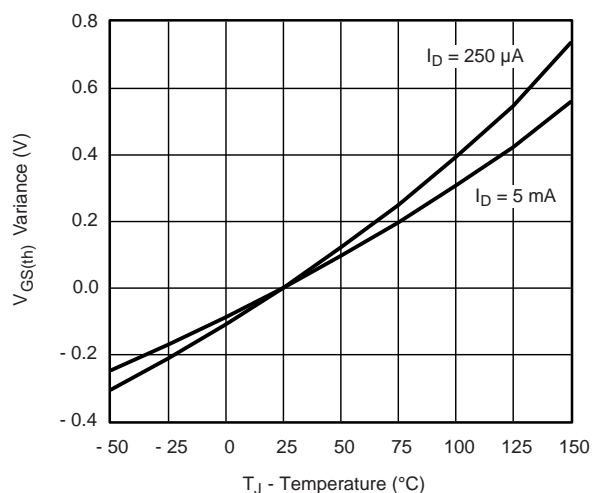
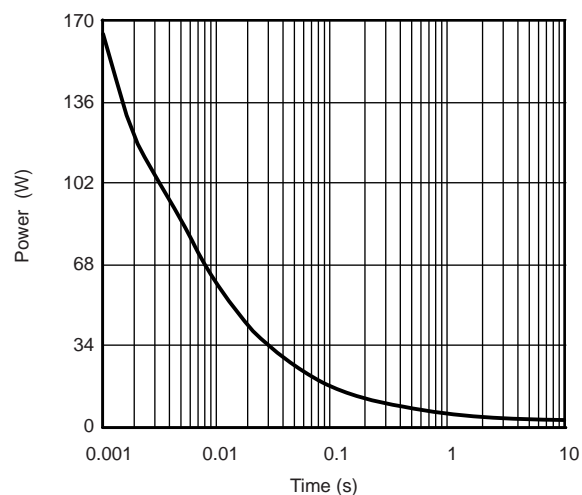
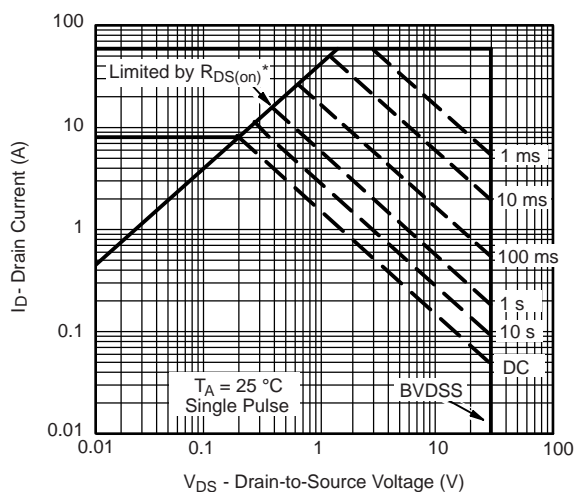
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

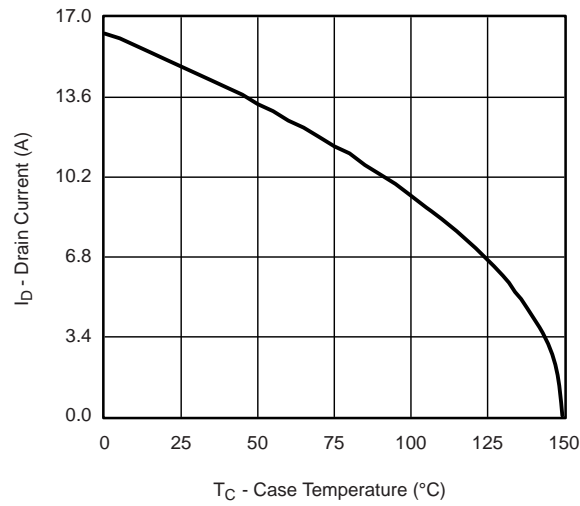
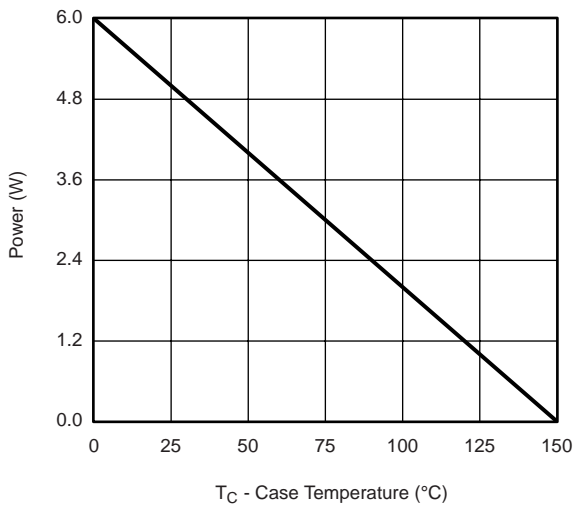
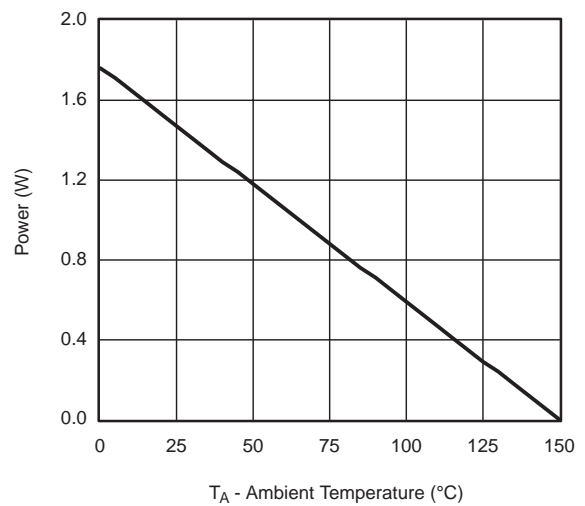
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

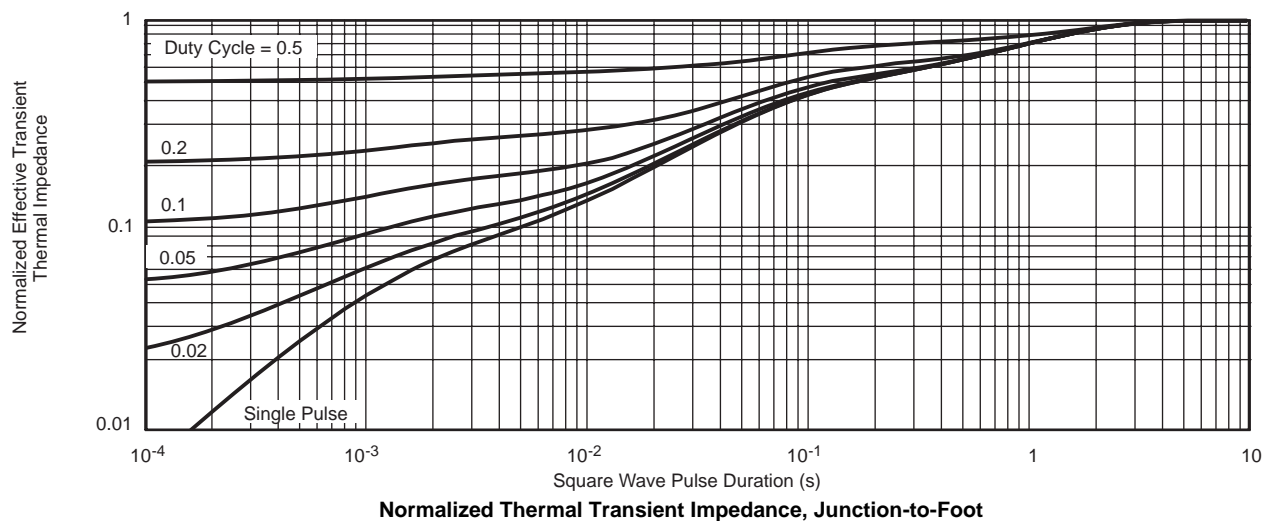
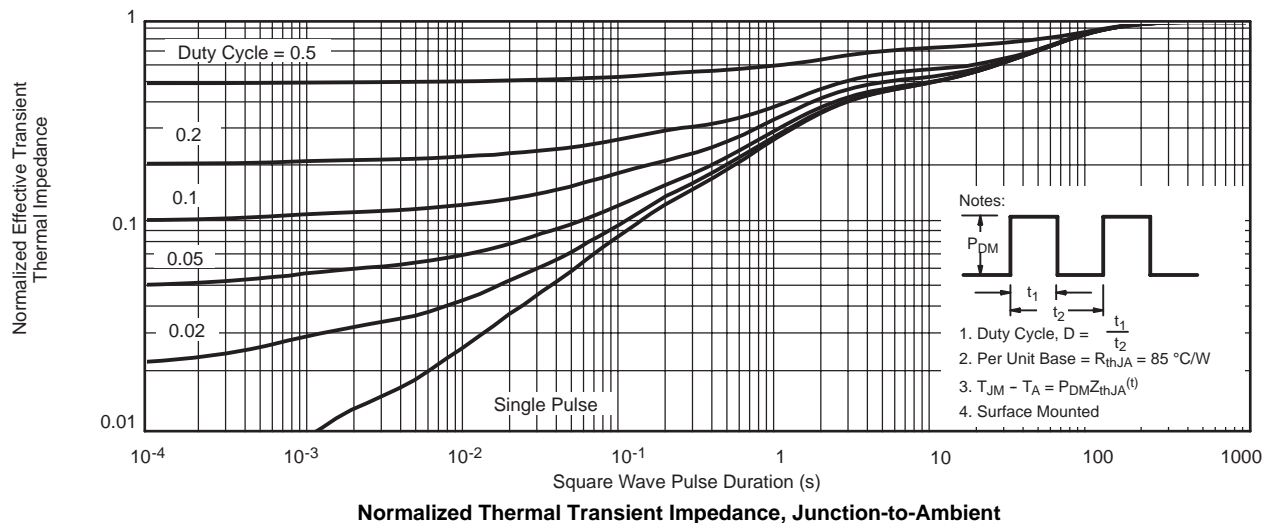
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Source-Drain Diode Forward Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

**Threshold Voltage**

**Single Pulse Power, Junction-to-Ambient**


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

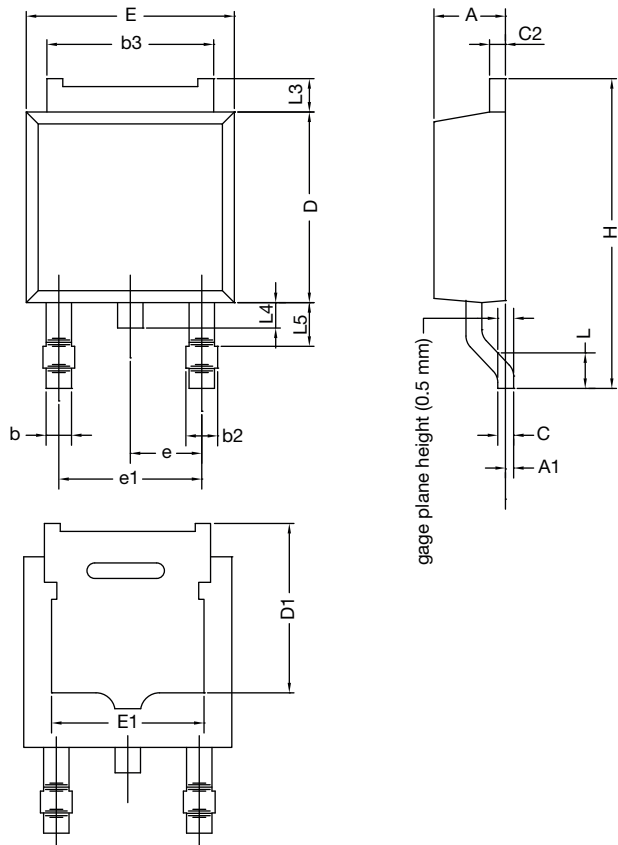
**Safe Operating Area**

**MOSFET TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Current Derating\***

**Power, Junction-to-Foot**

**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


TO-252AA CASE OUTLINE

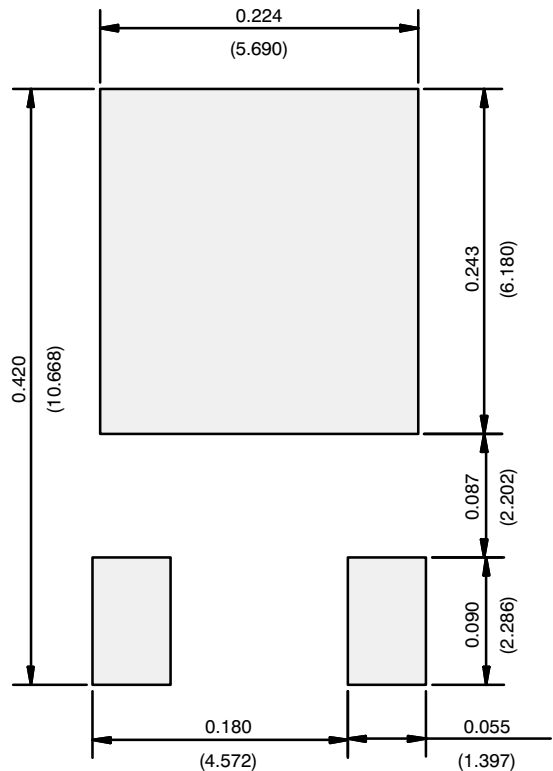


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12				
DWG: 5347				

**Note**

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)



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